

## ABSTRACT OF THE DISCLOSURE

According to the present invention, a feature of a waveguide type optical element and a method of manufacturing the same is to selectively diffuse Zn on a light absorption layer using an undope InP layer. Therefore, since impurity diffusion area is made on the light absorption layer under a ridge part, a depletion layer becomes thin in a thickness direction and an electric field can strongly be applied. Thereby, an extinction ratio characteristic of a device can be improved.